

General Description



The ICS87002-05 is a 1:2 LVCMOS/LVTTL low phase noise Zero Delay Buffer and is optimized for audio frequencies.

The device uses third generation FemtoClock® Technology for an optimum of high frequency and excellent phase jitter performance, combined with a low power consumption.

The device utilizes an internal feedback loop therefore eliminating the complexity of an external feedback loop.

The device utilizes a 3.3V supply and is packaged in a small, lead-free (RoHS 6) 8-lead SOIC package.

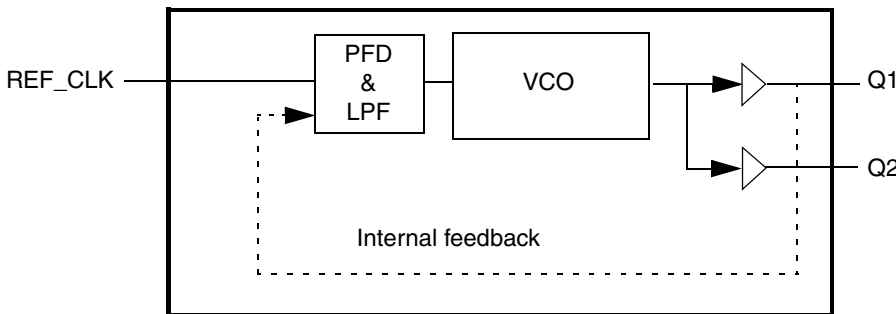
Features

- Third generation FemtoClock® technology
- Low phase noise zero delay buffer
- Low skew outputs
- One LVCMOS/LVTTL clock input
- Two LVCMOS/LVTTL outputs
- Phase noise: -125dBc/Hz @ 1kHz offset; -130dBc/Hz @ 100kHz offset
- Cycle-to-cycle jitter: 60ps (maximum)
- 0°C to 70°C ambient operating temperature
- Full 3.3V supply voltage

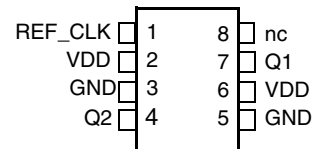
Supported Input Reference Clock Frequencies

REF_CLK Frequencies
11.2896MHz
12.288MHz
16.384MHz
16.9344MHz
18.432MHz
22.5792MHz
24.576MHz

Block Diagram



Pin Assignment



ICS87002-05
8-lead SOIC
3.8mm x 4.8mm x 1.47mm
M Package
Top View

Table 1. Pin Descriptions

Number	Name	Type	Description
1	REF_CLK	Input	Single-ended reference clock input. LVCMOS/LVTTL interface levels.
2, 6	V _{DD}	Power	Power supply pin.
3, 5	GND	Power	Power supply ground.
4, 7	Q2, Q1	Output	Single-ended clock outputs. 15Ω typical output impedance. LVCMOS/LVTTL interface level.
8	nc	Unused	No connect.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
C _{PD}	Power Dissipation Capacitance	V _{DD} = 3.6V		8		pF
R _{OUT}	Output Impedance	V _{DD} = 3.3V ± 0.3V		15		Ω

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{DD}	4.6V
Inputs, V	-0.5V to $V_{DD} + 0.5V$
Outputs, V_O	-0.5V to $V_{DD} + 0.5V$
Package Thermal Impedance, θ_{JA}	96°C/W (0 lfpm)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 3A. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 0.3V$, $T_A = 0^\circ C$ to $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{DD}	Power Supply Voltage		3.0	3.3	3.6	V
I_{DD}	Power Supply Current	No load			85	mA

Table 3B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = 3.3V \pm 0.3V$, $T_A = 0^\circ C$ to $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage		$(V_{DD}/2) + 1$			V
V_{IL}	Input Low Voltage				$(V_{DD}/2) - 1$	V
I_{IH}	Input High Current	$V_{DD} = 3.6V$			150	μA
I_{IL}	Input Low Current	$V_{DD} = 3.6V$	-150			μA
V_{OH}	Output High Voltage	$I_{OH} = -25mA$	2.4			V
V_{OL}	Output Low Voltage	$I_{OL} = 25mA$			0.4	V

AC Characteristics

Table 4. AC Characteristics, $V_{DD} = 3.3V \pm 0.3V$, $T_A = 0^\circ C$ to $70^\circ C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency; NOTE 1		11.2783		24.6005	MHz
$t_{sk(o)}$	Output Skew				20	ps
t_{PD}	Propagation Delay		200		1150	ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	425		1450	ps
i_{dc}	Input Duty Cycle	$f_{IN} = 24.576MHz$	30		70	%
o_{dc}	Output Duty Cycle	At $V_{DD}/2$	48		52	%
$\overline{f}_{jit(cc)}$	Cycle-to-cycle Jitter, NOTE 2, 3				60	ps
$\overline{f}_{jit(per)}$	Period Jitter (pk-pk), NOTE 2, 3			50	75	ps
	Long Term Jitter, NOTE 4	N = 512 Cycles		100	300	ps
	Phase Noise, Relative to Carrier; NOTE 5	1kHz offset		-125		dBc/Hz
		100kHz offset		-130		dBc/Hz

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE 1: Device operation is guaranteed for the standard audio reference frequencies of 11.2896MHz, 12.288MHz, 16.384MHz, 16.9344MHz, 18.432MHz, 22.5792MHz and 24.576MHz. A variation of up to $\pm 1000ppm$ in reference clock is acceptable at these frequencies.

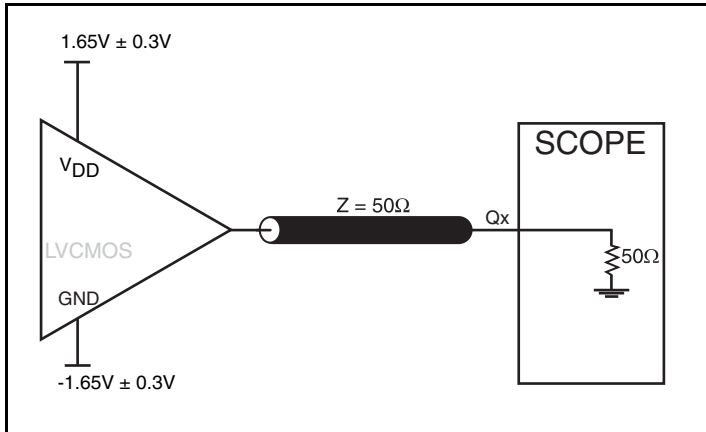
NOTE 2: Measured at 22.5792MHz and 24.576MHz input clock.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

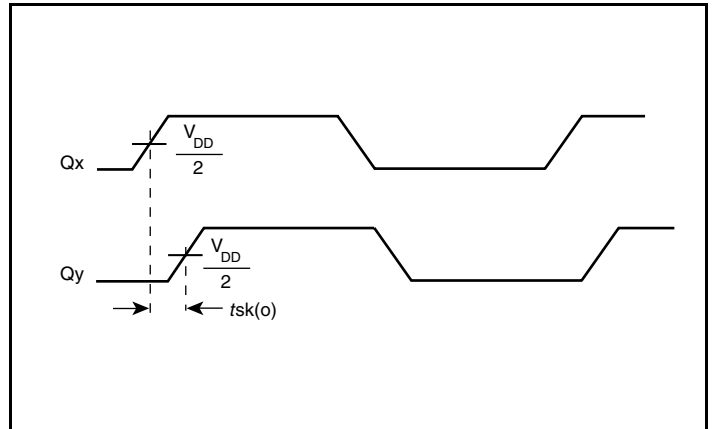
NOTE 4: Measured at 24.576MHz input clock and cycle N = 512.

NOTE 5: Measured at 24.576MHz input clock from 100Hz to 5MHz.

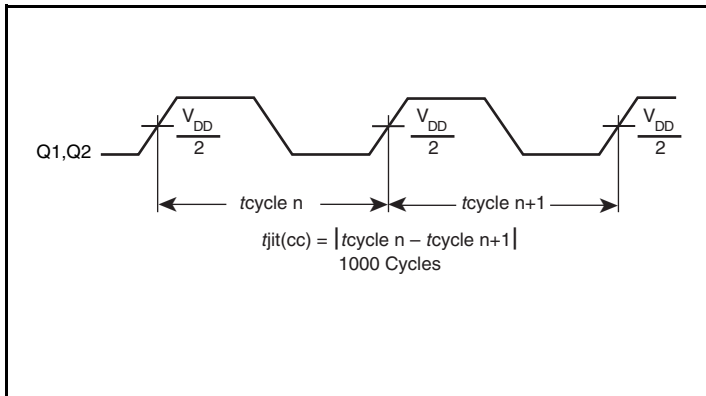
Parameter Measurement Information



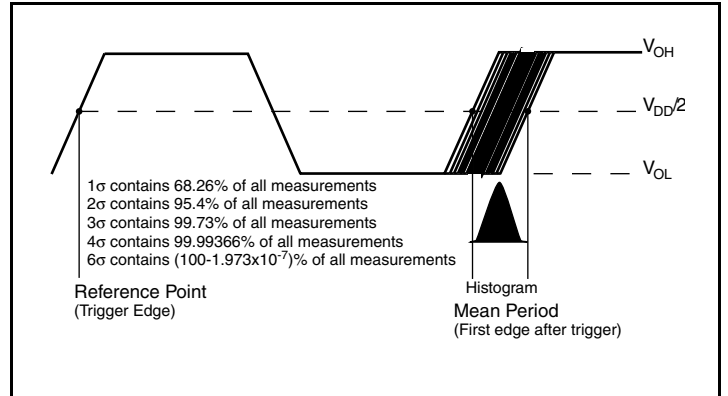
LVC MOS/LVTTL Output Load AC Test Circuit



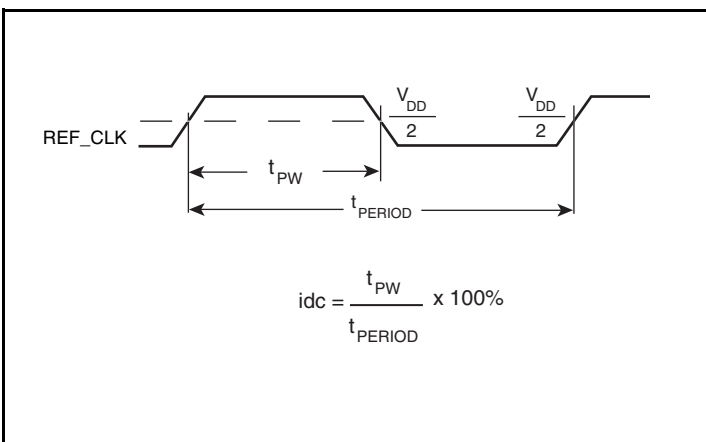
Output Skew



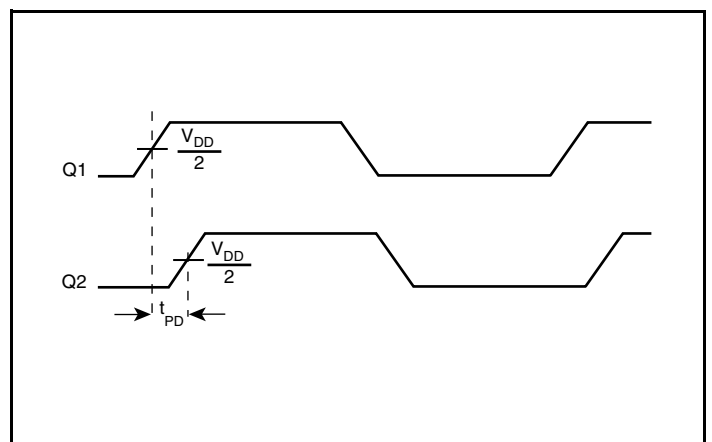
Cycle-to-Cycle Jitter



Period Jitter

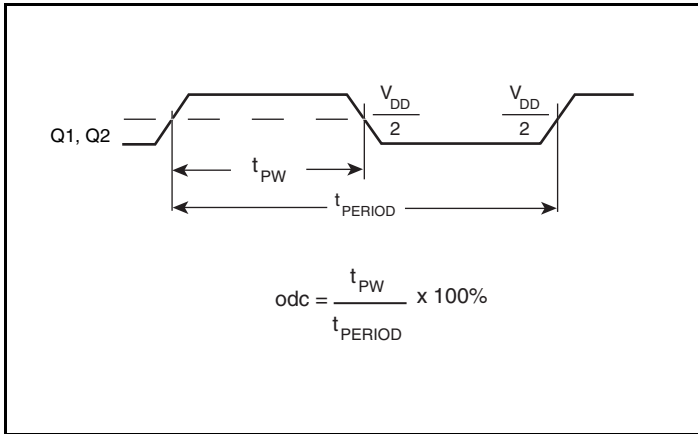


Input Duty Cycle

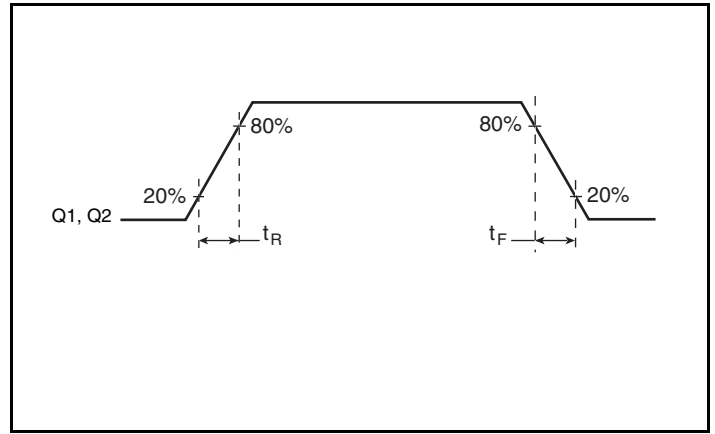


Propagation Delay

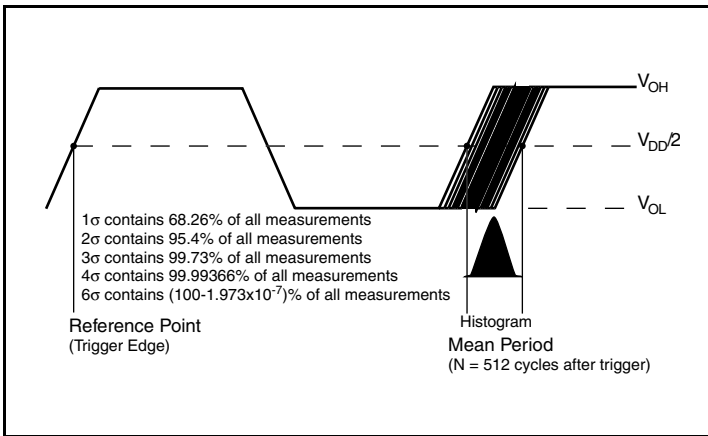
Parameter Measurement Information, continued



Output Duty Cycle/Pulse Width/Period



Output Rise/Fall Time



Long Term Jitter

Applications Information

Recommendations for Unused Output Pins

Outputs:

LVC MOS Outputs

All unused LVC MOS output can be left floating. There should be no trace attached.

Schematic Example

Figure 1 shows an example of ICS87002-05 application schematic. In this example, the device is operated at $V_{DD} = 3.3V$. The input is driven by a 3.3V LVCMOS driver. One example of an LVCMOS

termination is shown in this schematic. The decoupling capacitors should be located as close as possible to the power pin.

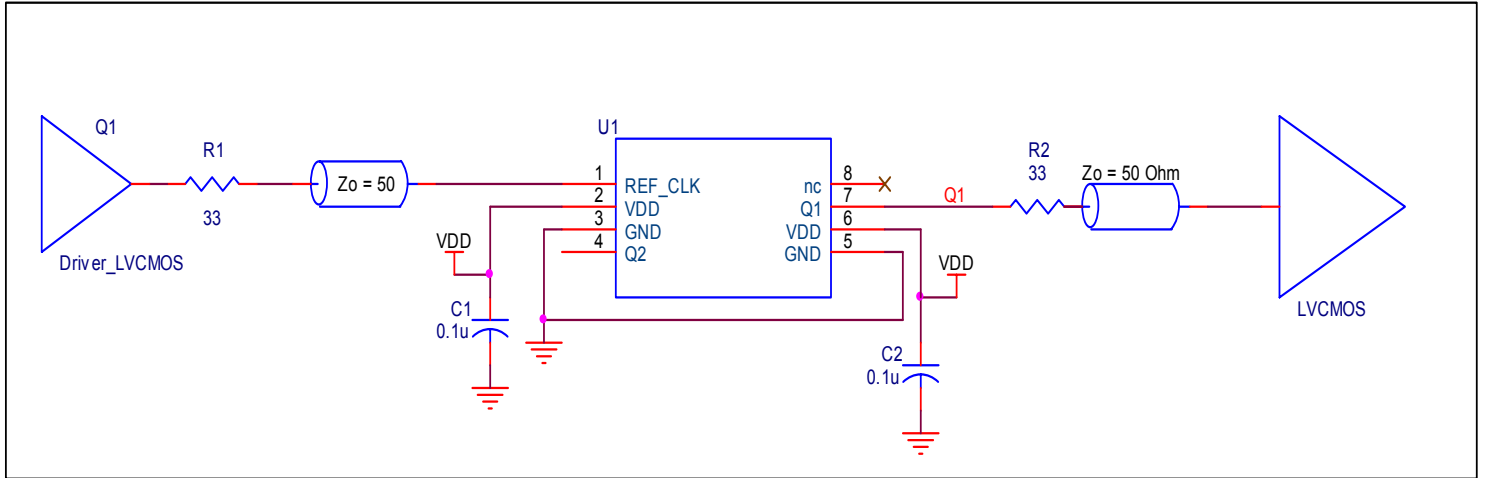


Figure 1. ICS87002-05 Schematic Example

Power Considerations

This section provides information on power dissipation and junction temperature for the ICS87002-05. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS87002-05 is the sum of the core power plus the power dissipation in the load(s). The following is the power dissipation for $V_{DD} = 3.3V + 0.3V = 3.6V$, which gives worst case results.

$$\text{Power (core)}_{MAX} = V_{DD_MAX} * I_{DD} = 3.6V * 85mA = \mathbf{306mW}$$

Total Static Power:

$$= \text{Power (core)}_{MAX} = \mathbf{306mW}$$

Dynamic Power Dissipation at F_{OUT_MAX} (24.576MHz)

$$\text{Total Power (} F_{OUT_MAX} \text{)} = [(C_{PD} * N) * \text{Frequency} * (V_{DDO})^2] = [(8pF * 2) * 24.576MHz * (3.6V)^2] = \mathbf{5.1mW \text{ per output}}$$

N = number of outputs

Total Power

$$\begin{aligned} &= \text{Static Power} + \text{Dynamic Power Dissipation} \\ &= 306mW + 5.1mW \\ &= \mathbf{311mW} \end{aligned}$$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, T_j , to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 96°C/W per Table 5 below.

Therefore, T_j for an ambient temperature of 70°C with all outputs switching is:

$$70^\circ\text{C} + 0.311W * 96^\circ\text{C/W} = 99.9^\circ\text{C}. \text{ This is below the limit of } 125^\circ\text{C}.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 5. Thermal Resistance θ_{JA} for 8 Lead SOIC, Forced Convection

Meters per Second	θ_{JA} by Velocity		
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	96.0°C/W	87°C/W	82.0°C/W

Reliability Information

Table 6. θ_{JA} vs. Air Flow Table for an 8-lead SOIC

θ_{JA} vs. Air Flow			
Linear Feet per Minute			
Multi-Layer PCB, JEDEC Standard Test Boards	96°C/W	87°C/W	82°C/W

Transistor Count

The transistor count for ICS87002-05 is: 2267

Package Outline and Package Dimensions

Package Outline - M Suffix for 8 Lead SOIC

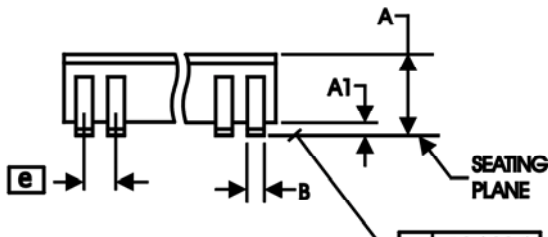
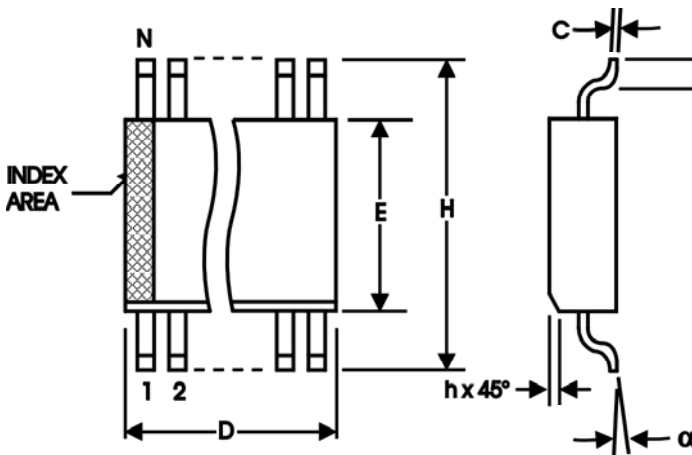


Table 7. Package Dimensions

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	8	
A	1.35	1.75
A1	0.10	0.25
B	0.33	0.51
C	0.19	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 Basic	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.27
α	0°	8°

Reference Document: JEDEC Publication 95, MS-012

Ordering Information

Table 8. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
87002BM-05LF	P0003	Lead-Free, 8-lead SOIC	Tube	0°C to 70°C
87002BM-05LFT	P0003	Lead-Free, 8-lead SOIC	2500 Tape & Reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant

Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	4	4	AC Characteristics Table - changed Min. and Max. f_{OUT} values. NOTE 1 - changed $\pm 100\text{pm}$ to $\pm 1000\text{ppm}$.	4/16/10

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